

## ABSTRACT

A method is provided for reducing Critical Dimension (CD) non-uniformity in creating a patterned layer of semiconductor material. Two masking layers are respectively created, the first masking layer comprising a main pattern, an isolated pattern and a dummy pattern, the second masking layer exposing the dummy pattern. Methods of compensating for optical proximity effects and micro-loading, as provided by the invention, are applied in creating the first masking layer. The patterned first masking layer is transposed to an underlying layer creating a first pattern therein. The second masking layer removes the dummy features from the transposed first pattern, creating a second pattern therein comprising a main pattern and an isolated pattern to which compensation for optical proximity effects and micro-loading have been applied. The second pattern serves for additional etching of underlying semiconductor material.